

AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Previously Presented) A component comprising:

a chip having a first chip face and a second chip face, the first chip face comprising component structures and connector metallizations associated with the component structures;

a frame structure on the first chip face and adjacent to the component structures;

a cover over the frame structure, the cover having a first cover face and a second cover face, the first cover face being closer to the chip than the second cover face;

a back metallization that is on the second chip face, on sides of the frame structure, and on sides of the cover;

a contact on the second cover face; and

a connection through the cover, the connection electrically connecting the component structures and the contact;

wherein the connection is metallized and sealed.
2. (Previously Presented) The component of claim 1, wherein the chip and the cover define a cavity that contains the component structures.

3. (Previously Presented) The component of claim 1, wherein the frame structure comprises one or more interior structures that define one or more enclosures within the frame structure, the one or more enclosures exposing the connector metallizations.

4. (Currently Amended) The component of claim 1, further comprising wiring adjacent to the first cover face, the wiring being connected to the ~~the~~ connector metallizations and to the connection.

5. (Previously Presented) The component of claim 1, further comprising, between the cover and the frame structure:

at least one intermediate layer; and
wiring adjacent to the first cover face.

6. (Previously Presented) The component of one of claims 4 or 5, wherein the wiring comprises metal structures comprising at least one of conductors and passive components, the passive components comprising at least one of capacitors, inductors, and resistors.

7. (Currently Amended) The component of claim 1, wherein the cover
[[[]]]comprises one of ceramic, metal, and glass; and
wherein the frame structure comprises one of benzocyclobutene, polyimide, and benzoxazol.

8. (Previously Presented) The component of claim 1, wherein the component is at least one of a microelectronic component, a surface wave component, an FBAR resonator, a micro-optic component, a micromechanical component, and a hybrid component.

9. (Previously Presented) The component of claim 2, wherein the cavity contains a protective gas having a spark-over resistance that is different from a spark-over resistance of air.

10. (Previously Presented) The component of claim 1, wherein the connection is conical in shape.

11. (Previously Presented) A method of producing encapsulated components, comprising:

adding component structures to a first face of a wafer;

applying a frame structure to the first face of the wafer, the frame structure surrounding the component structures;

adhering a cover to the frame structure thereby forming a cavity between the cover and the wafer, the component structures being inside the cavity, wherein the cover comprises a first cover face and a second cover face, the second cover face being nearer to the wafer than the first cover face, the first cover face comprising a contact, and wherein

the cover comprises a connection that electrically connects the component structures to the contact, the connection being sealed with a diffusion-proof underside metallization;

forming cuts in a second face of the wafer that does not include the component structures, the cuts passing through the frame structure and into the cover, wherein the second face of the wafer comprises metallization; and

separating the wafer into individual components along the cuts.

12. (Previously Presented) The method of claim 11, further comprising:
applying an intermediate layer, the intermediate layer being between the frame structure and the cover; and

adding wiring to the intermediate layer, the wiring being connected to a metallization on the wafer via the connection.

13. (Previously Presented) The method of claim 12, wherein the intermediate layer comprises a cover film that is glued to the frame structure.

14. (Previously Presented) The method of claim 13, wherein applying the intermediate layer comprises:

applying the cover film and an ancillary film to the frame structure;

structuring the cover film; and

removing the ancillary film.

15. (Previously Presented) The method of claim 14, wherein the cover film is applied to the ancillary film as a reaction resin in viscous form, and wherein structuring comprising laminating and curing.

16. (Previously Presented) The method of claim 11, wherein applying the frame structure comprises shaping the frame structure.

17. (Currently Amended) The method of claim 12, wherein the frame structure and/or the intermediate layer (~~ZS~~) are applied via photo-structuring, etching using a resist mask, or laser ablation.

18. (Previously Presented) The method of claim 11, further comprising:
forming the metallization and the diffusion-proof underside metallization by sputtering; and
reinforcing the metallization and the diffusion-proof underside metallization via wet chemistry or galvanization.

19. (Previously Presented) The method of claim 18, wherein the metallization is formed over an entire area of the second surface of the wafer; and
wherein forming the metallization and/or the diffusion-proof underside metallization comprises structuring the metallization and/or the diffusion-proof underside metallization.

20. (Previously Presented) The method of claim 12, further comprising:
applying a protective coating to the component structures before the wiring is
added; and
removing the protective coating after the wiring is added.

21. (Previously Presented) The method of claim 11, further comprising:
roughening a surface of the wafer at a contact point with the frame structure prior
to applying the frame structure.

22. (Previously Presented) The method of claim 12, wherein applying the
intermediate layer comprises shaping the intermediate layer.